

CRYSTAL GROWTH METHOD

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Abstract

PURPOSE: To provide a crystal growth method improved in the efficiency of use of a feedstock gas at the time of growing III-V compound semiconductor crystal with the use of atomic layer epitaxy method in the crystal growth method using the atomic layer epitaxy method for alternately supplying feedstock gases out of crystal growth techniques of compound semiconductor.

CONSTITUTION: In a crystal growth method using atomic layer epitaxy method for growing III-V compound semiconductor crystal on a semiconductor substrate surface by alternately supplying group III feedstock gas and group V feedstock gas, the linear velocity of the group V feedstock gas flowing on the semiconductor substrate surface at the time of growing the crystal is made slower than the linear velocity of group III feedstock gas.